

< Silicon RF Power MOS FET (Discrete) >

RD08MUS2

RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

DESCRIPTION

RD08MUS2 is a MOS FET type transistor specifically designed for VHF/UHF RF power amplifiers applications.

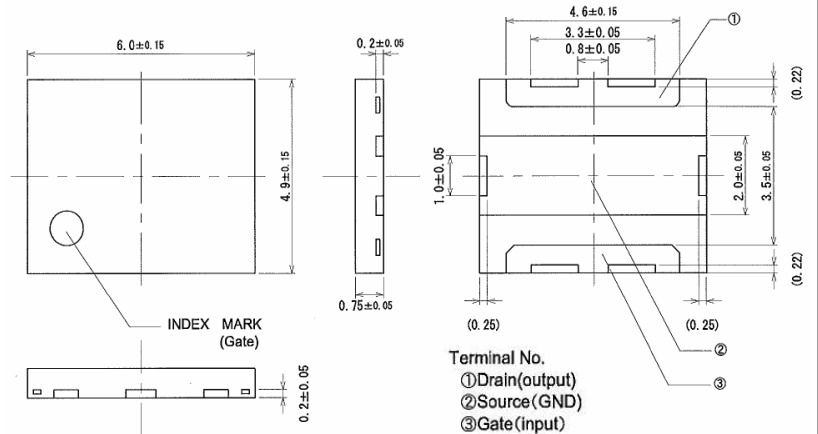
FEATURES

High power gain and High Efficiency.
 $P_{out}=7.5W_{min}$, Drain Effi. $\approx 62\%_{min}$
 @ $V_{ds}=7.2V$, $I_{dq}=280mA$, $P_{in}=0.2W$, $f=527MHz$
 Integrated gate protection diode.

APPLICATION

For output stage of high power amplifiers in VHF/UHF-band mobile radio sets.

OUTLINE DRAWING



Terminal No.
 ① Drain(output)
 ② Source(GND)
 ③ Gate(input)

Note
 (): center value

UNIT:mm

RoHS COMPLIANT

RD08MUS2 is a RoHS compliant product.

ORDERING INFORMATION

ORDER NUMBER	SUPPLY FORM
RD08MUS2-601	Pallet (25pcs/pallet), for evaluation
RD08MUS2-T612	Tape & Reel (2,000pcs/reel)
RD08MUS2-T614	Tape & Reel (4,000pcs/reel)

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ABSOLUTE MAXIMUM RATINGS (Tc=25°C UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	RATINGS	UNIT
VDSS	Drain to source voltage	VGS=0V	25	V
VGSS	Gate to source voltage	VDS=0V	-5/+10	V
Pch*	Channel dissipation	Tc=25°C	46	W
Pin	Input Power	Zg=Zl=50Ω	0.8	W
Pout	Output Power	Zg=Zl=50Ω	10	W
ID	Drain Current	-	3.0	A
Tch	Junction Temperature	-	150	°C
Tstg	Storage temperature	-	-40 to +125	°C

Note: Above parameters are guaranteed independently.

* Theoretical value in case of mounted on infinite heat sink.

ELECTRICAL CHARACTERISTICS (Tc=25°C, UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX.	
IDSS	Drain cutoff current	VDS=17V, VGS=0V	-	-	50	uA
IGSS	Gate cutoff current	VGS=5V, VDS=0V	-	-	1	uA
VTH	Gate threshold Voltage	VDS=7.2V, IDS=1mA	0.5	1	1.5	V
Pout	Output power	f=527MHz, VDD=7.2V	7.5*	8.5*	-	W
ηD	Drain efficiency	Pin=0.2W, Idq=280mA	62*	65*	-	%
VSWRT	Load VSWR tolerance	VDS=9.5V, Po=7.5W(Pin Control) f=135MHz, Idq=280mA, Zg=50Ω Load VSWR=20:1(All Phase)	No destroy**			-

Note: Above parameters, ratings, limits and conditions are subject to change.

* In Mitsubishi 527MHz Test fixture with clamping mechanism.

** In Mitsubishi 135MHz Test fixture with clamping mechanism.

TEMPERATURE CHARACTERISTICS (Tc=25°C UNLESS OTHERWISE NOTED)

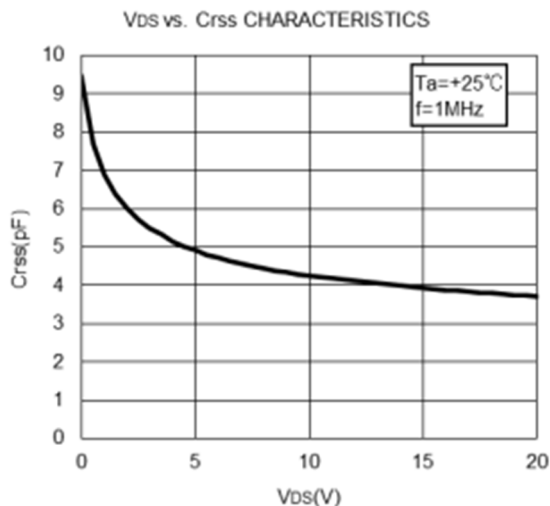
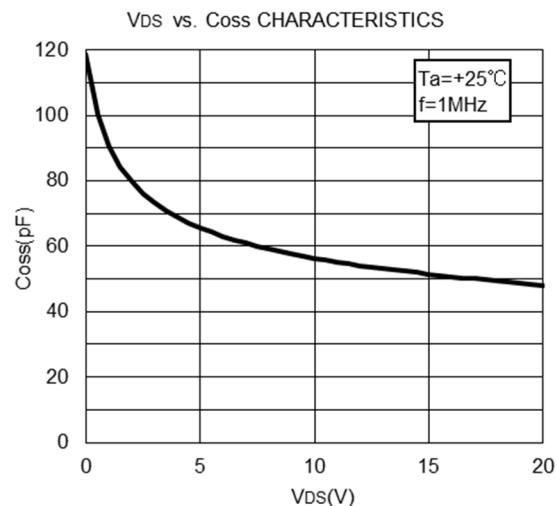
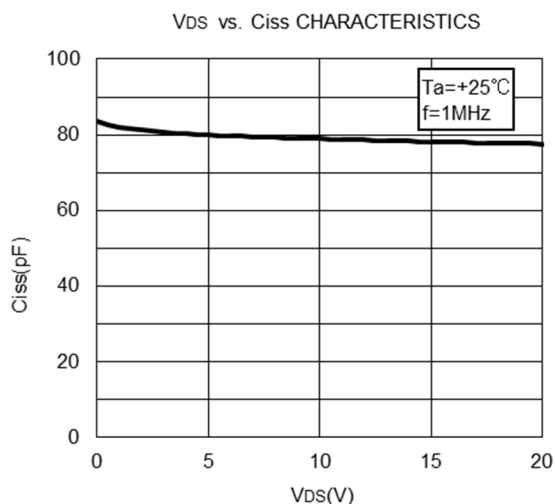
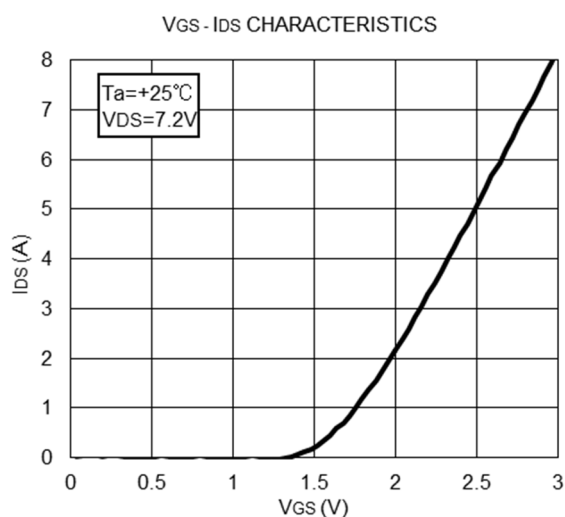
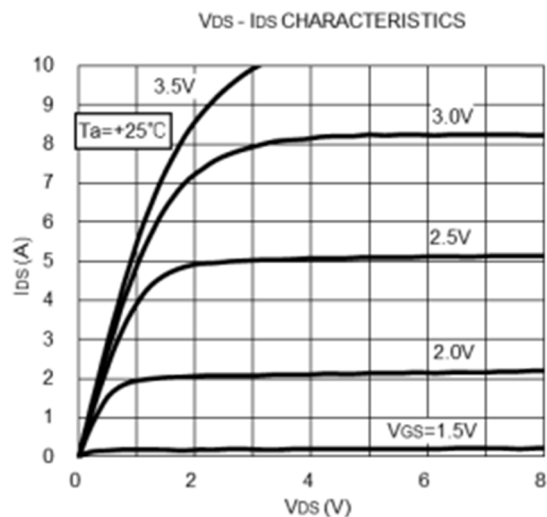
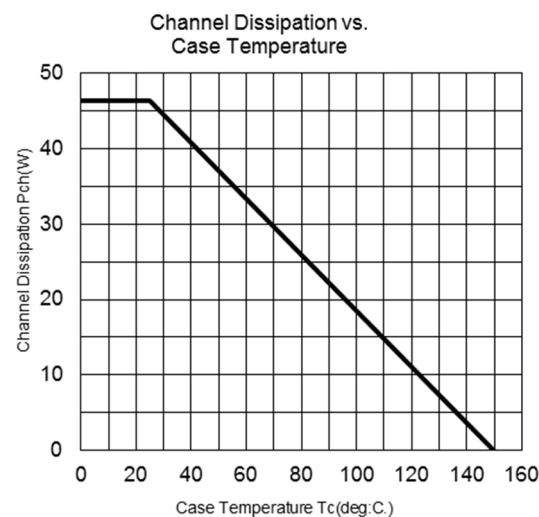
SYMBOL	PARAMETER	CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
Rth(j-c)	Thermal Resistance	Junction to Case	-	2.0	2.7	°C /W

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TYPICAL CHARACTERISTICS

(These are only typical curves and devices are not necessarily guaranteed at these curves.)



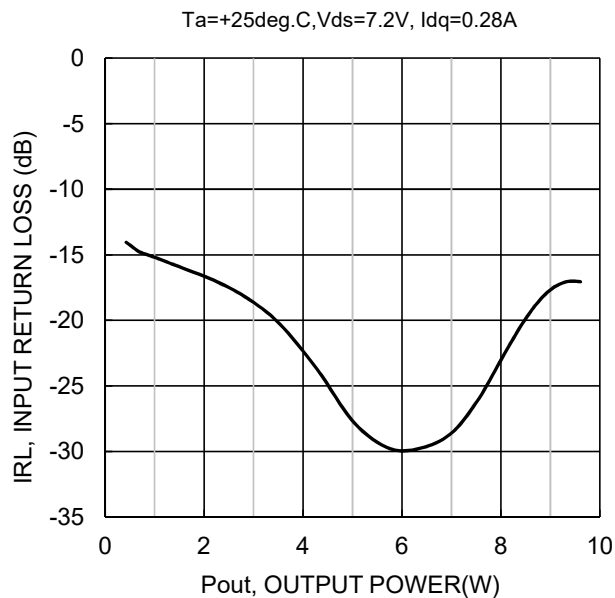
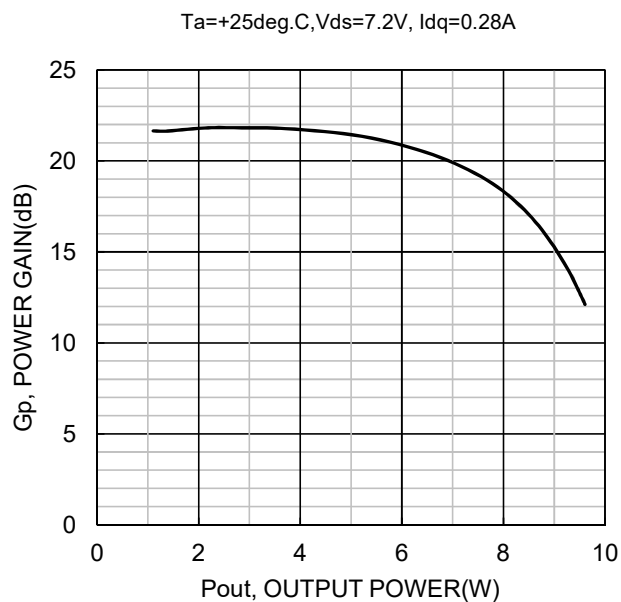
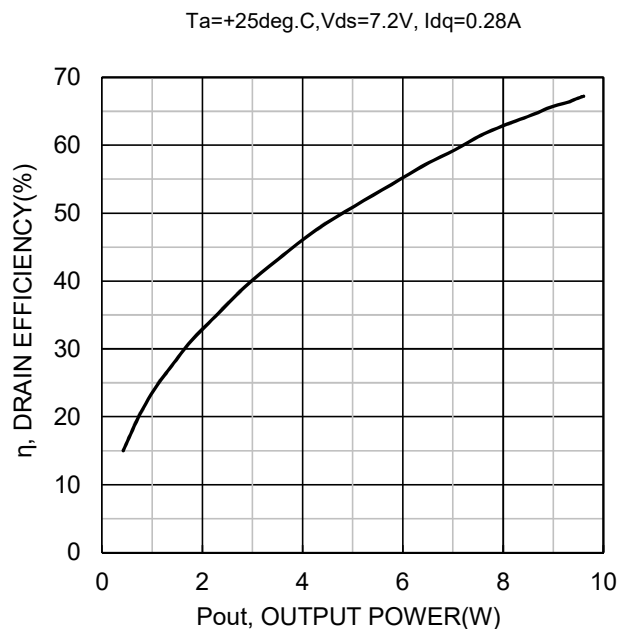
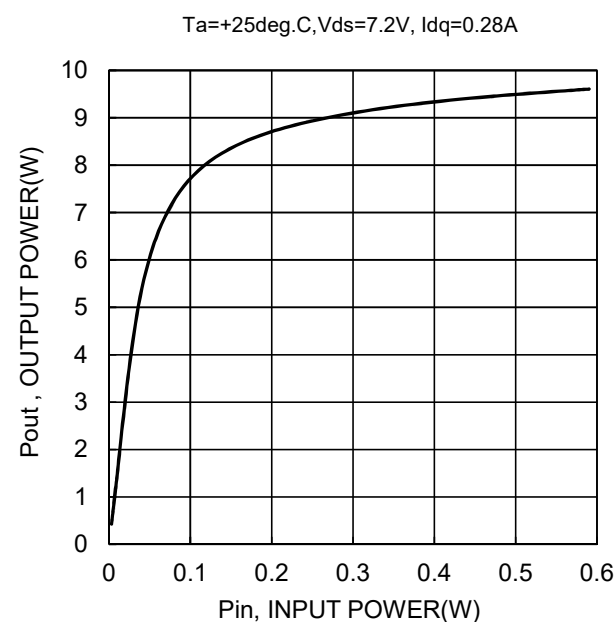
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Measured on 527MHz Narrow Band Test Fixture

TYPICAL CHARACTERISTICS (f=527MHz)

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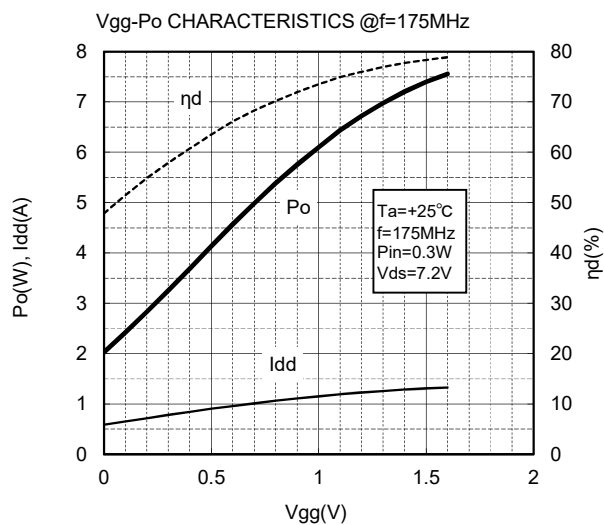
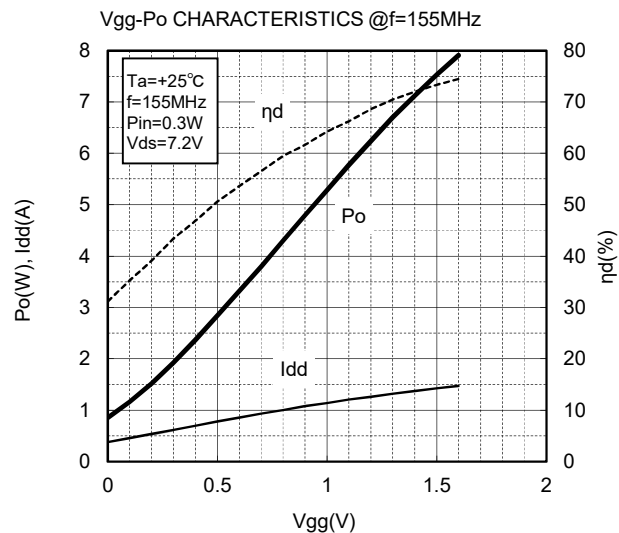
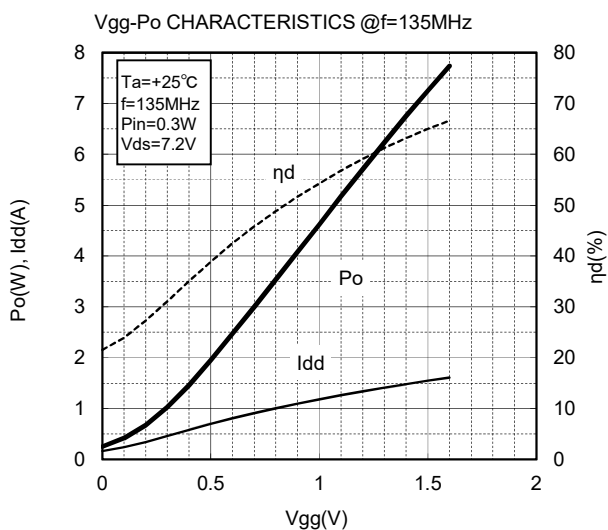
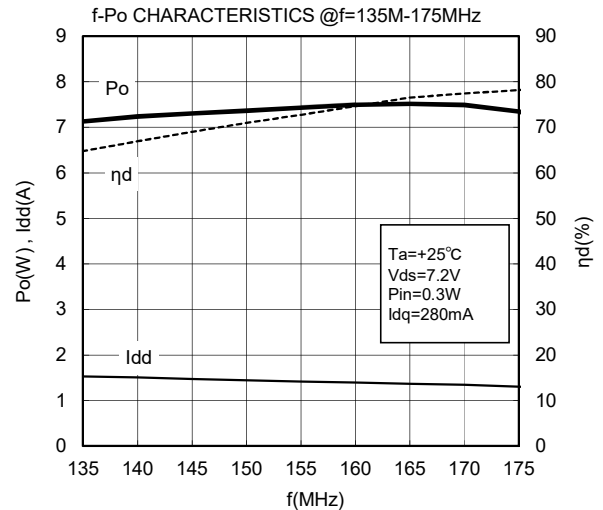
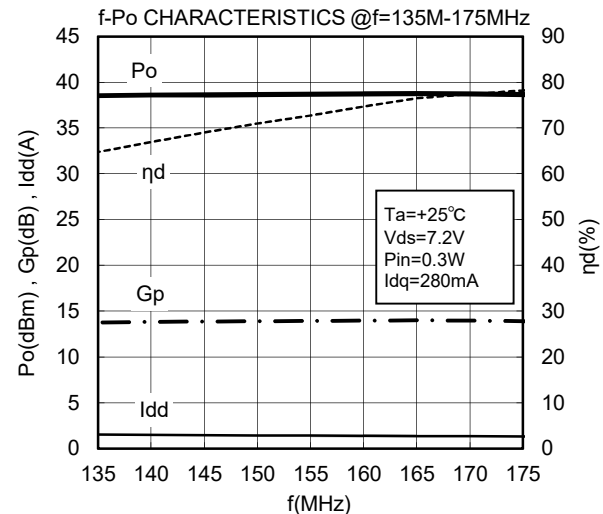


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TYPICAL CHARACTERISTICS ($f=135\text{-}175\text{MHz}$, $T_a=+25^\circ\text{C}$)

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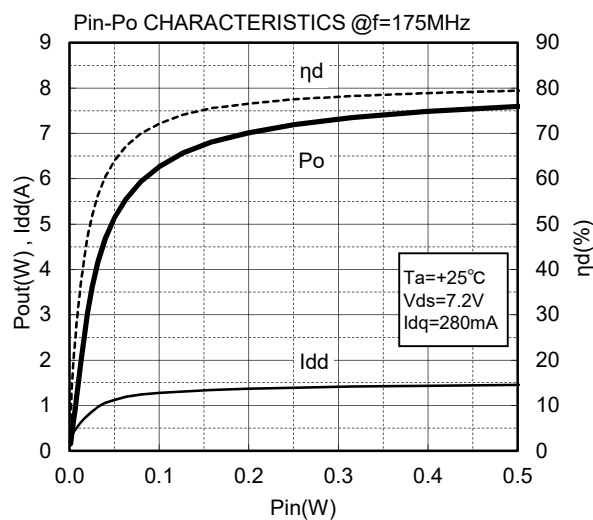
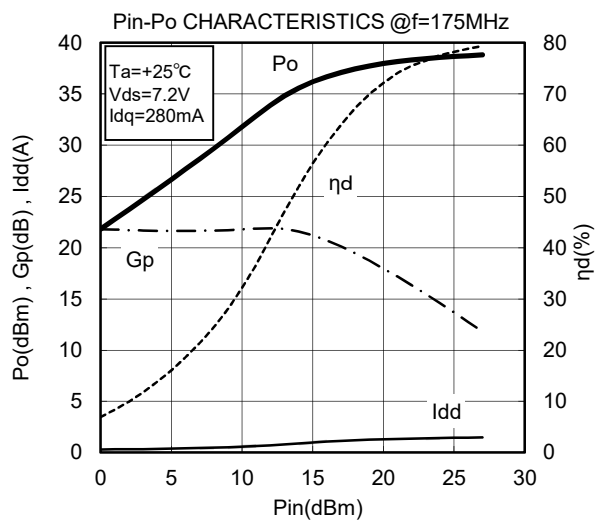
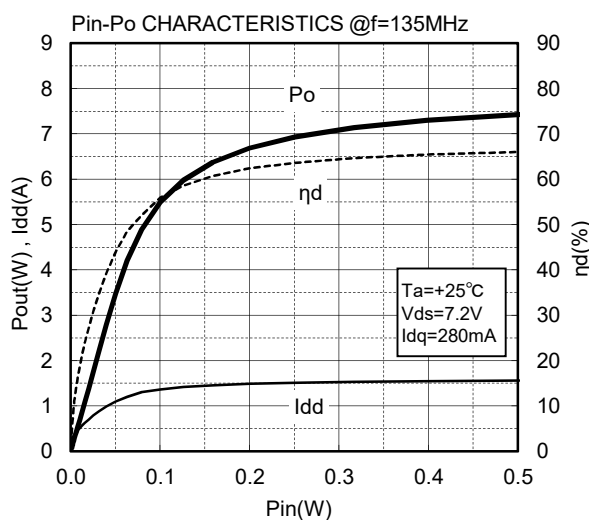
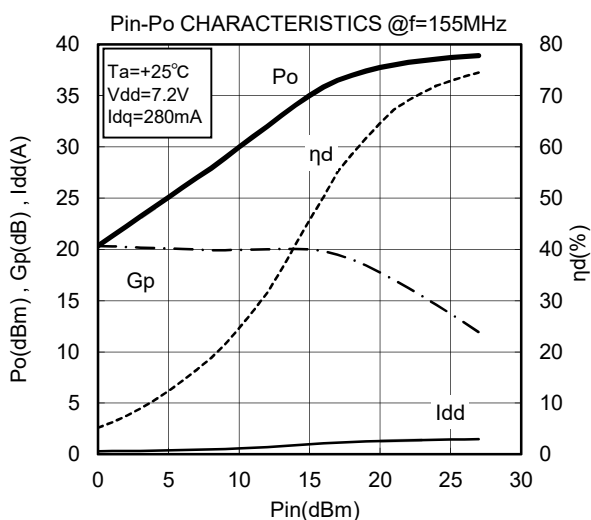
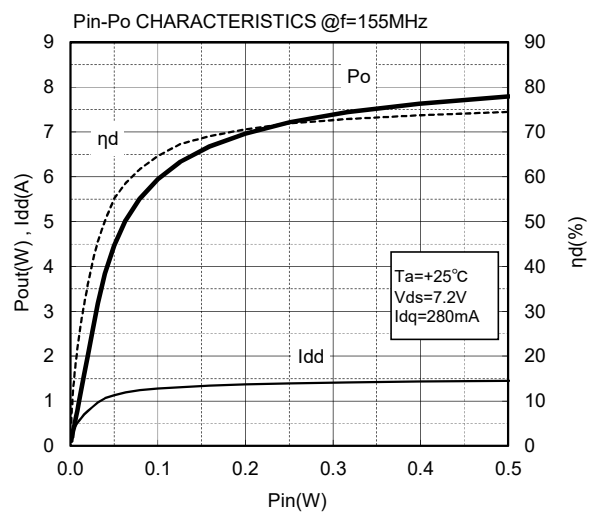
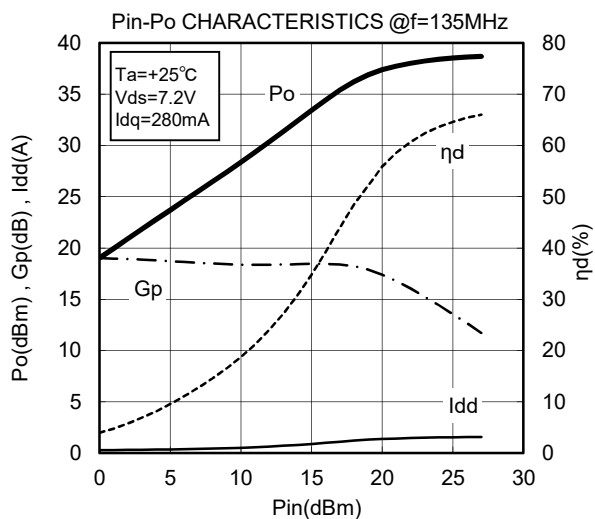


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TYPICAL CHARACTERISTICS ($f=135\text{--}175\text{MHz}$, $T_a=+25^\circ\text{C}$)

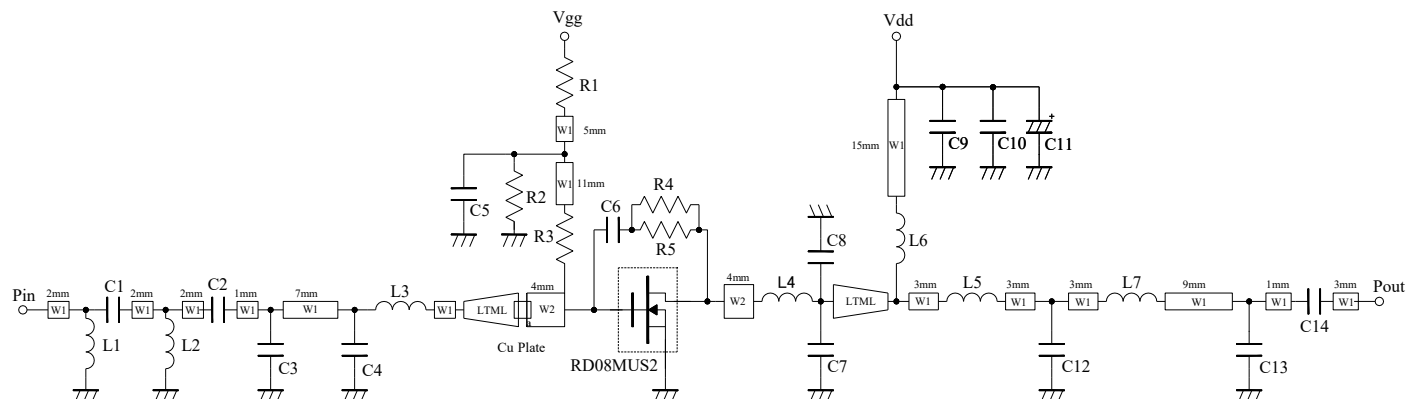
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EQUIVALENT CIRCUITRY for VHF Circuit for f=135-175MHz



Note: Board Material -Glass- Epoxy Substrate

er=4.8, t=0.6mm, W1=1mm, W2=6mm

LTML: Linear tapered microstrip line (w1=1.0mm, w2=6.0mm, L=2.7mm)

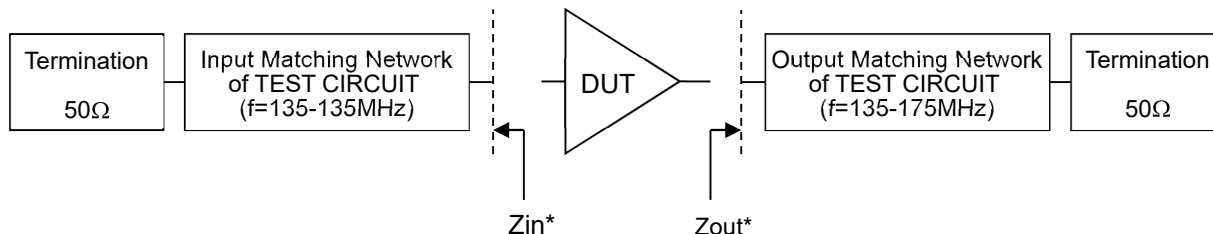
Parts Type		Value	Type name	Vender
Capacitor	C1	30pF	GRM1882C1H300JA01D	Murata Manufacturing Co., Ltd.
	C2	51pF	GRM1882C1H510JA01D	Murata Manufacturing Co., Ltd.
	C3	27pF	GRM1882C1H270JA01D	Murata Manufacturing Co., Ltd.
	C4	43pF	GRM1882C1H430JA01D	Murata Manufacturing Co., Ltd.
	C5	1000pF	GRM2162C1H102JA01D	Murata Manufacturing Co., Ltd.
	C6	47pF	GRM1882C1H470JA01D	Murata Manufacturing Co., Ltd.
	C7	68pF	GQM1882C1H680JB01D	Murata Manufacturing Co., Ltd.
	C8	68pF	GQM1882C1H680JB01D	Murata Manufacturing Co., Ltd.
	C9	0.22μF	GRM21BR71H224KA01D	Murata Manufacturing Co., Ltd.
	C10	100pF	GRM2162C1H101JA01D	Murata Manufacturing Co., Ltd.
	C11	22μF	A0603	NICHICON CORPORATION
	C12	33pF	GQM1882C1H330JB01D	Murata Manufacturing Co., Ltd.
	C13	12pF	GQM1882C1H120JB01D	Murata Manufacturing Co., Ltd.
	C14	100pF	GQM1882C1H101JB01D	Murata Manufacturing Co., Ltd.
Resistance	R1	33k Ω	RPC05-333	Taiyosha Electric Co.,Ltd.
	R2	33k Ω	RPC05-333	Taiyosha Electric Co.,Ltd.
	R3	10 Ω	RPC05-100	Taiyosha Electric Co.,Ltd.
	R4	390 Ω	RPC05-391	Taiyosha Electric Co.,Ltd.
	R5	390 Ω	RPC05-391	Taiyosha Electric Co.,Ltd.
Inductance	L1	100 nH(Chip Inductor)	LQG18HNR10J00	Murata Manufacturing Co., Ltd.
	L2	56 nH(Chip Inductor)	LQG18HN56NJ00	Murata Manufacturing Co., Ltd.
	L3	12nH Enameled wire 3Turns, Diameter:0.23mm,φ1.62mm(the out side diameter)	2303A	Yoneda Processing Place Co.,Ltd.
	L4	10nH Enameled wire 5Turns, Diameter:0.4mm,φ1.6mm (the out side diameter)	4805A	Yoneda Processing Place Co.,Ltd.
	L5	17nH Enameled wire 4Turns, Diameter:0.23mm,φ1.62mm (the out side diameter)	2304C	Yoneda Processing Place Co.,Ltd.
	L6	37nH Enameled wire 7Turns, Diameter:0.4mm,φ2.46mm(the out side diameter)	4007C	Yoneda Processing Place Co.,Ltd.
	L7	24nH Enameled wire 5Turns, Diameter:0.23mm,φ1.62mm(the out side diameter)	2305C	Yoneda Processing Place Co.,Ltd.

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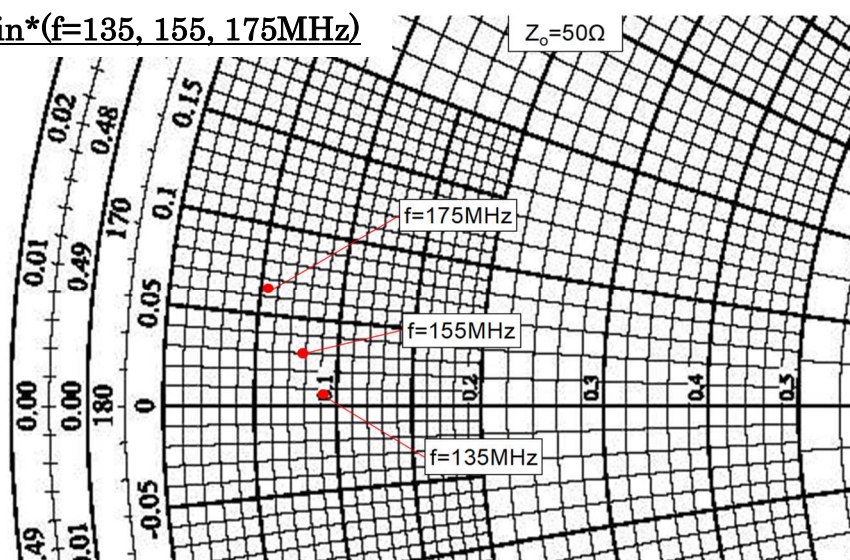
RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

Input / Output Impedance VS. Frequency Characteristics for f=135-175MHz

Method of Measurement

 Z_{in}^* : Input Matching Network impedance measured from DUT Z_{out}^* : Output Matching Network impedance measured from DUT Z_0 : Characteristic impedance

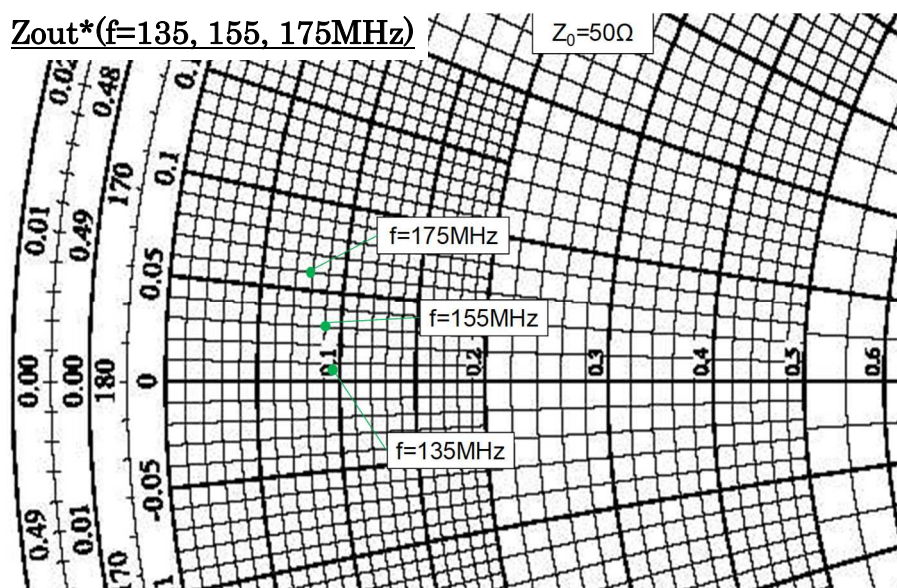
$Z_{in}^*(f=135, 155, 175\text{MHz})$



f (MHz)	Z_{in}^* (Ω)
135	4.53 + j 0.38
155	3.86 + j 1.47
175	3.38 + j 2.72

 Z_{in}^* : Complex conjugate of input impedance

$Z_{out}^*(f=135, 155, 175\text{MHz})$



f (MHz)	Z_{out}^* (Ω)
135	4.82 + j 0.44
155	4.52 + j 1.94
175	4.00 + j 3.02

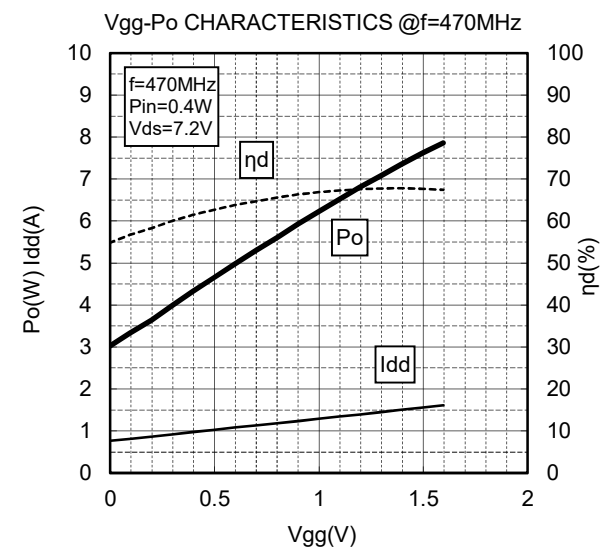
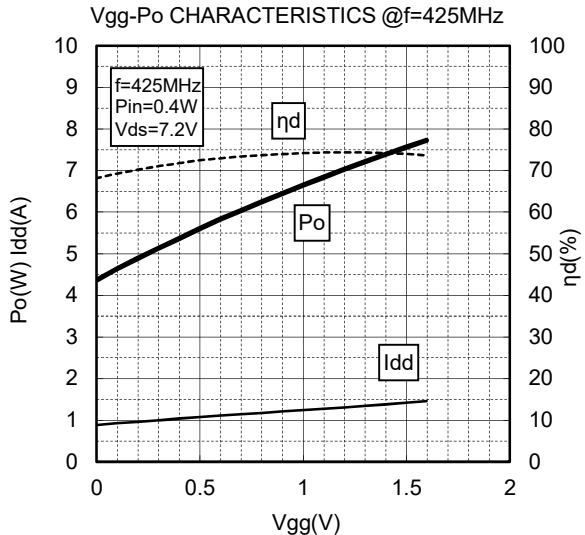
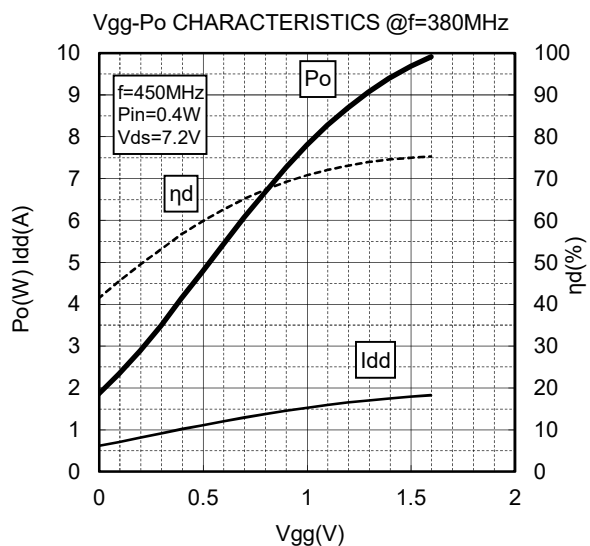
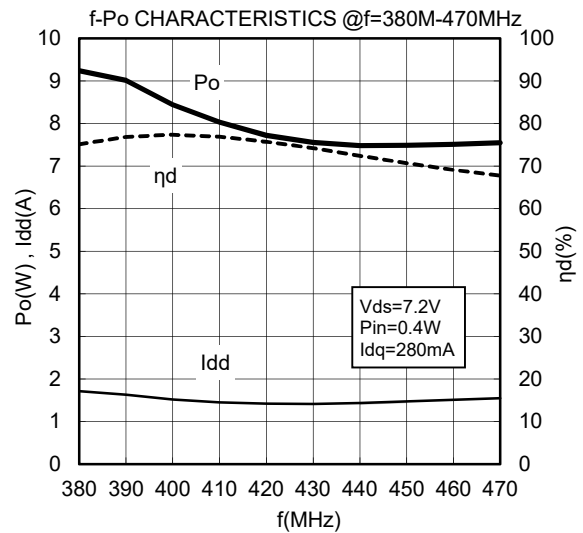
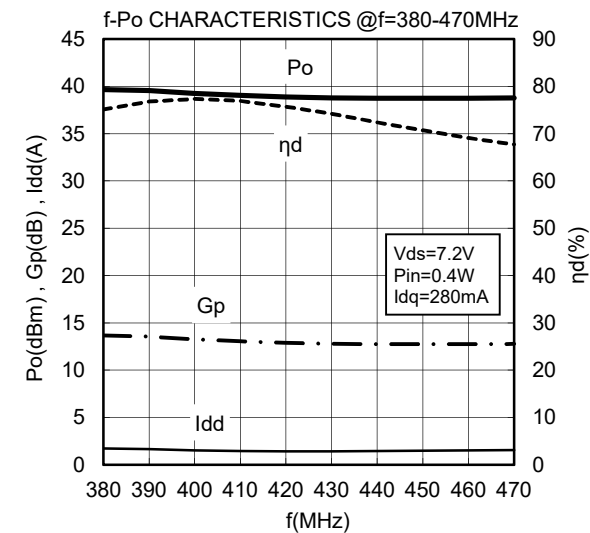
 Z_{out}^* : Complex conjugate of output impedance

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TYPICAL CHARACTERISTICS (f=380-470MHz, Ta=+25°C)

(These are only typical curves and devices are not necessarily guaranteed at these curves.)

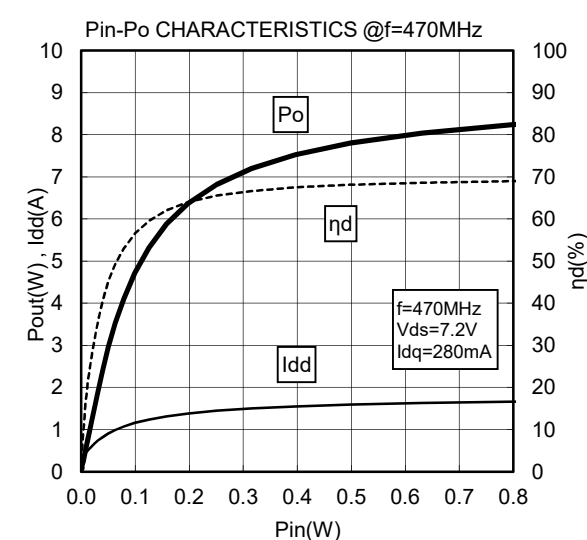
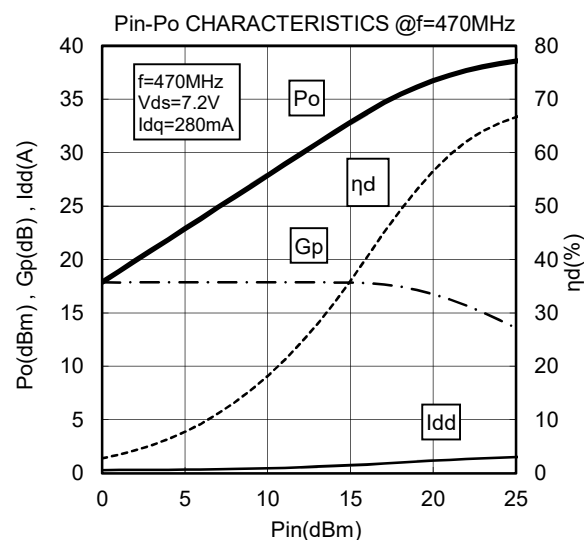
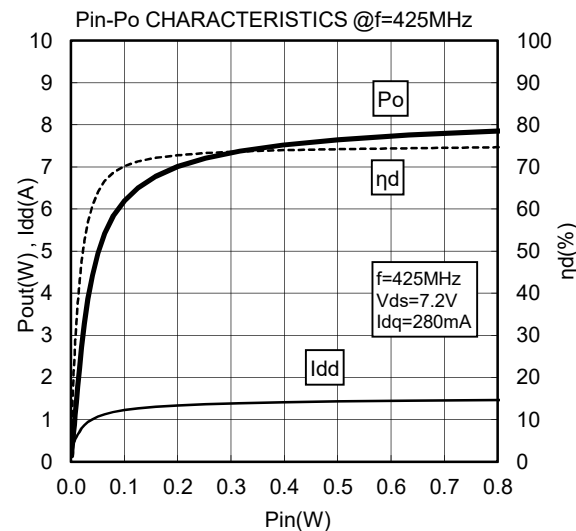
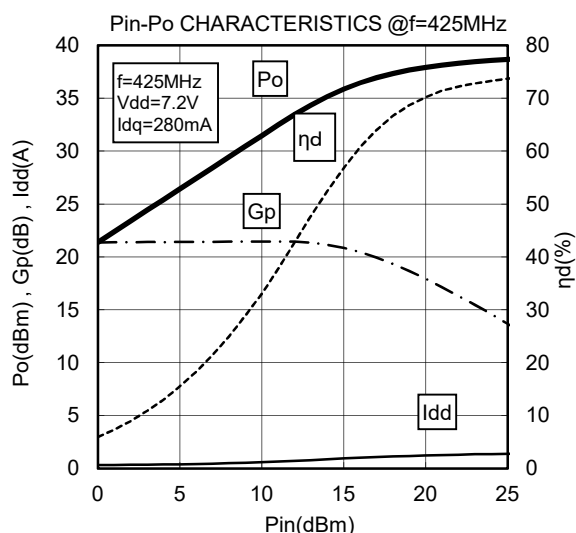
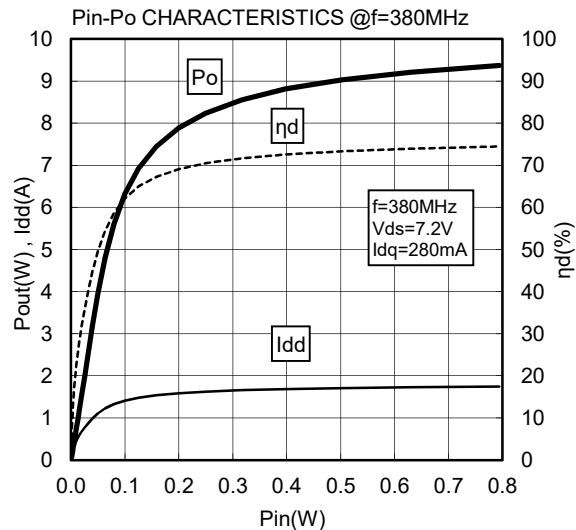
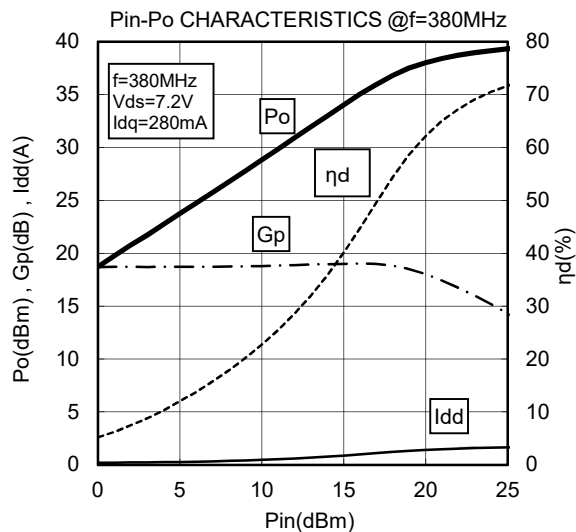


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TYPICAL CHARACTERISTICS (f=380-470MHz)

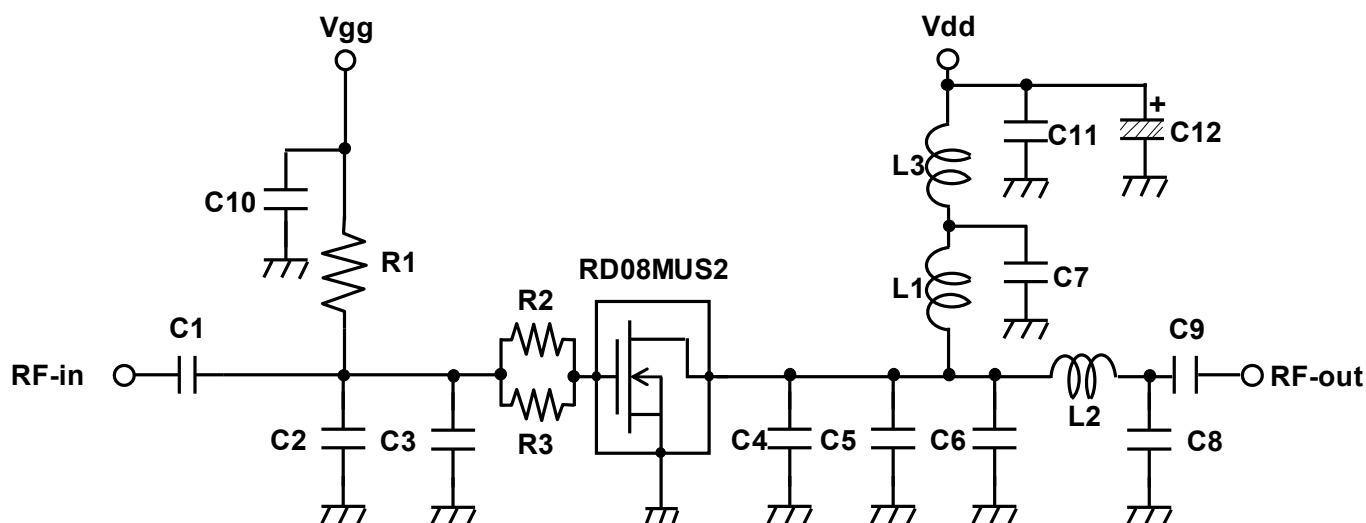
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RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

EQUIVALENT CIRCUITRY for UHF Circuit for f=380-470MHz



<Note>

Board material - Glass-Epoxy Substrate(ϵ_r :4.8, t :0.8mm)Micro strip Line width = 1.3mm / 50 Ω

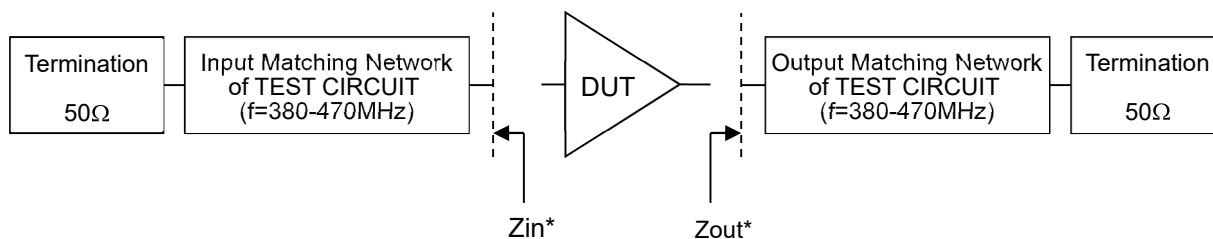
Part	Description	Part number	Manufacturer
C1, C9	100 pF	GRM2162C1H101JA01	MURATA MANUFACTURING CO.
C2	22 pF	GRM21A5C2D220JW01	MURATA MANUFACTURING CO.
C3	33 pF	GRM21A5C2D330JW01	MURATA MANUFACTURING CO.
C4	56 pF	GQM2192C1H560JB01	MURATA MANUFACTURING CO.
C5	22 pF	GQM2192C1H220JB01	MURATA MANUFACTURING CO.
C6, C8	12 pF	GRM21A5C2D120JW01	MURATA MANUFACTURING CO.
C7	8 pF	GRM1882C1H8R0CA01	MURATA MANUFACTURING CO.
C10, C11	1000 pF	GRM2162C1H102JA01	MURATA MANUFACTURING CO.
C12	22 μ F	UVZ1H220MDD	NICHICON CORPORATION
L1, L2	1 nH Copper bridge	-	-
L3	25nH Enameled wire 5Turns, Diameter:0.40mm, ϕ 2.46mm (the out side diameter)	4005A	Yoneda Processing Place Co.,Ltd.
R1	2.2 k Ω	RPC05 222-J	TAIYOSHA ELECTRIC CO.
R2, R3	1 Ω	RPC05 1R0-J	TAIYOSHA ELECTRIC CO.

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input / Output Impedance VS. Frequency Characteristics for f=380-470MHz

Method of Measurement

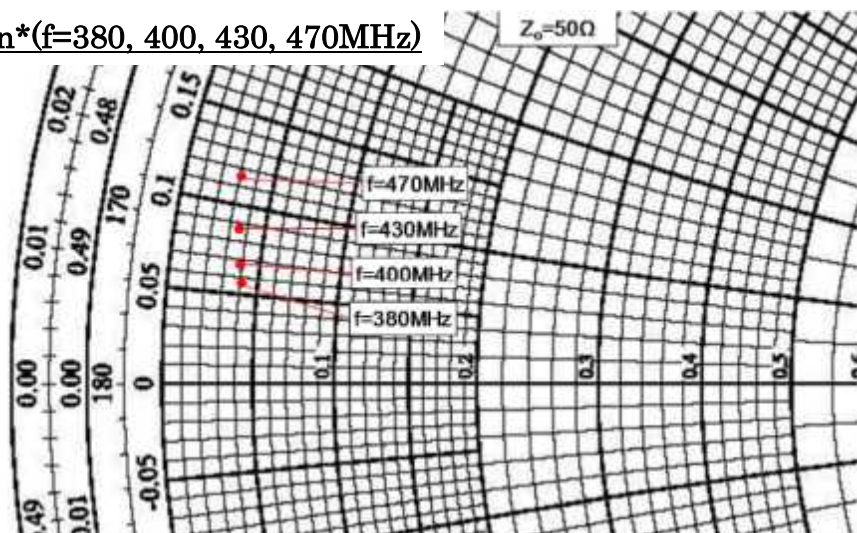


Z_{in}^* : Input Matching Network impedance measured from DUT

Z_{out}^* : Output Matching Network impedance measured from DUT

Z_0 : Characteristic impedance

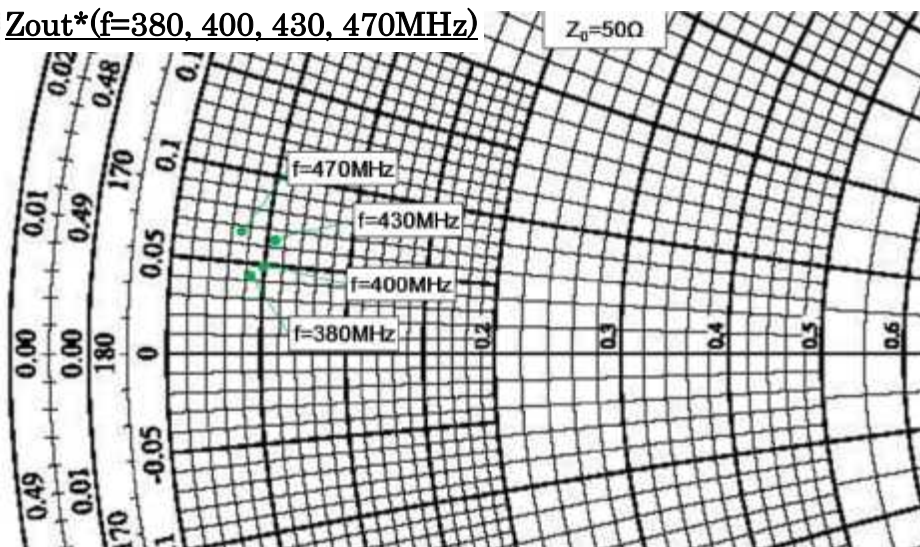
$Z_{in}^*(f=380, 400, 430, 470\text{MHz})$



f (MHz)	Z_{in}^* (Ω)
380	2.17 + j 2.55
400	2.02 + j 3.31
430	1.88 + j 4.37
470	2.09 + j 5.92

Z_{in}^* : Complex conjugate of input impedance

$Z_{out}^*(f=380, 400, 430, 470\text{MHz})$



f (MHz)	Z_{out}^* (Ω)
380	2.18 + j 2.08
430	2.51 + j 2.47
430	3.14 + j 2.58
470	3.45 + j 1.80

Z_{out}^* : Complex conjugate of output impedance

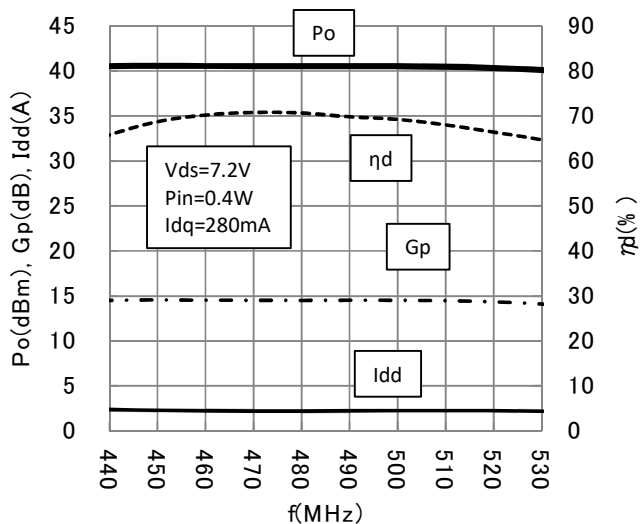
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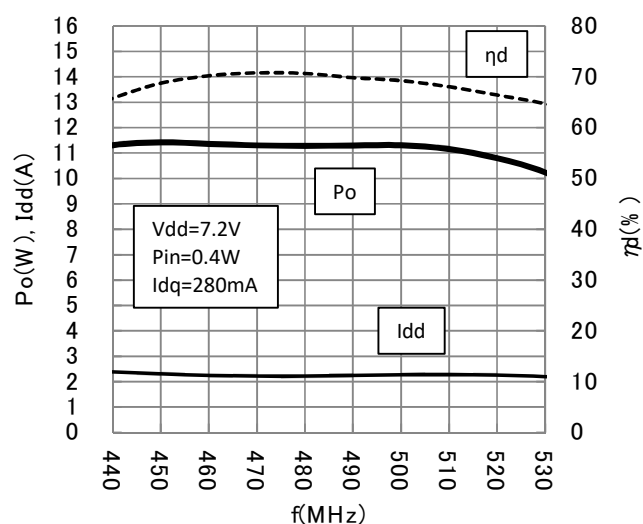
TYPICAL CHARACTERISTICS ($f=450\text{--}530\text{MHz}$, $T_a=+25^\circ\text{C}$)

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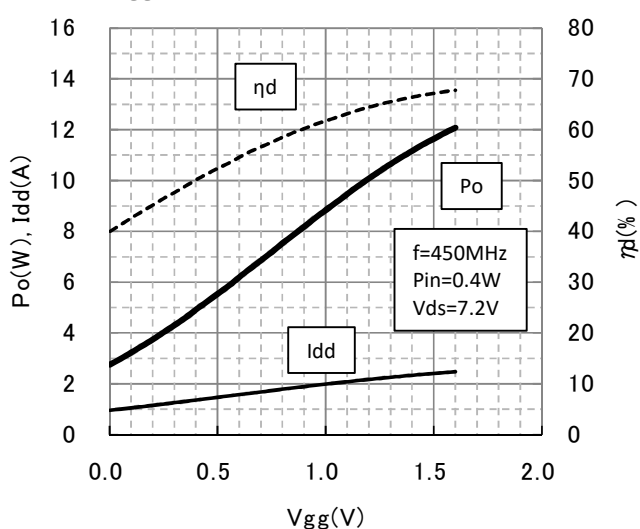
f-Po CHARACTERISTICS @ $f = 440\text{--}530\text{MHz}$



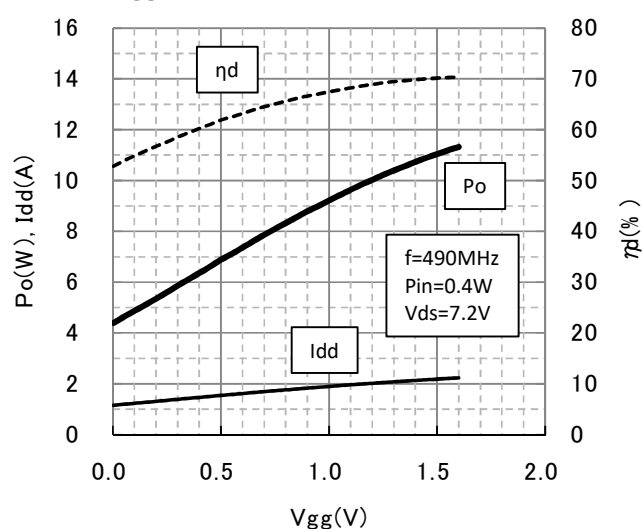
f-Po CHARACTERISTICS @ $f = 440\text{--}530\text{MHz}$



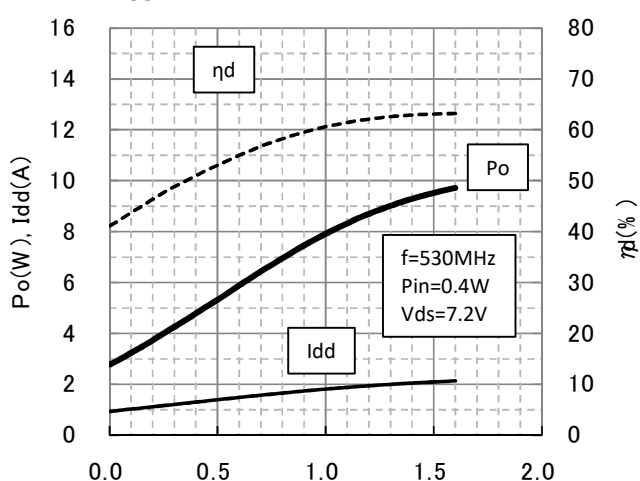
Vgg-Po CHARACTERISTICS @ $f = 450\text{MHz}$



Vgg-Po CHARACTERISTICS @ $f = 490\text{MHz}$



Vgg-Po CHARACTERISTICS @ $f = 530\text{MHz}$

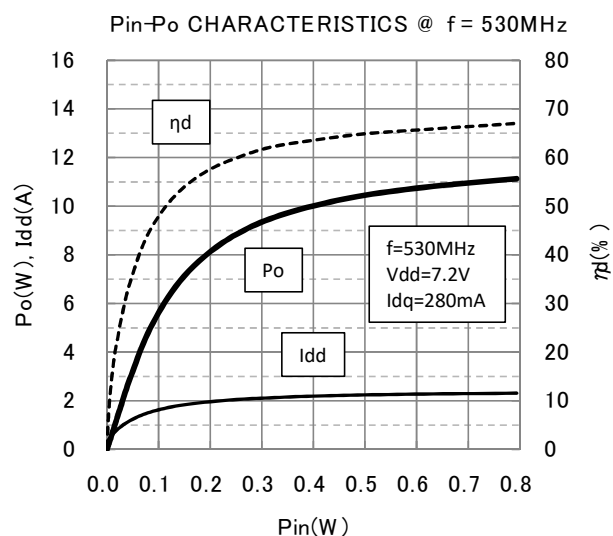
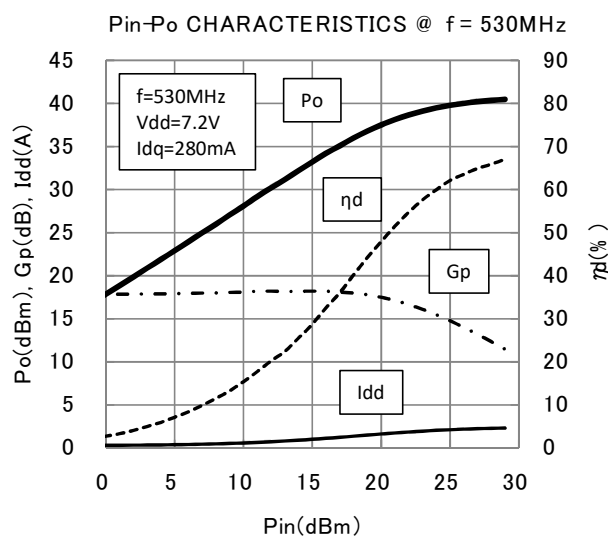
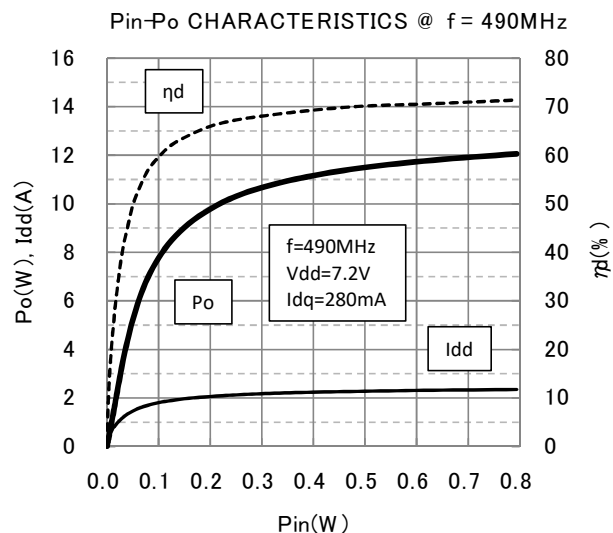
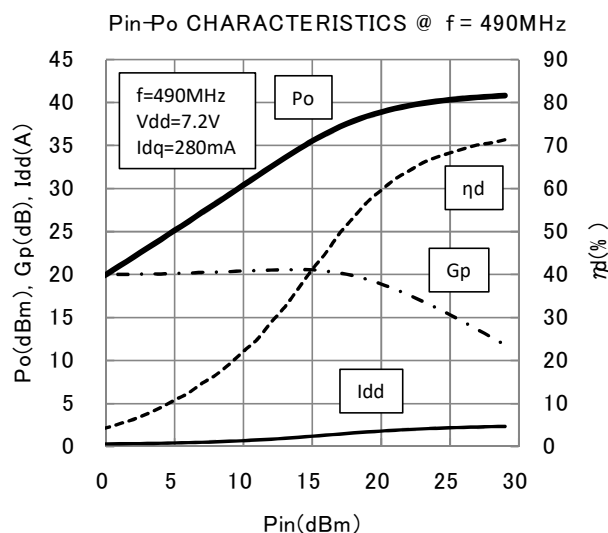
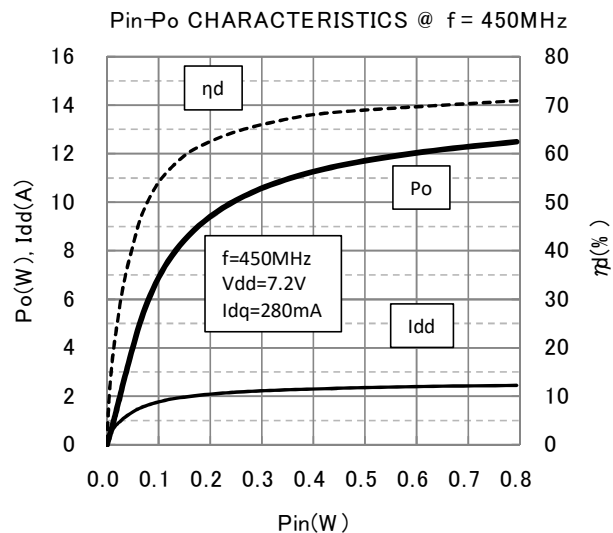
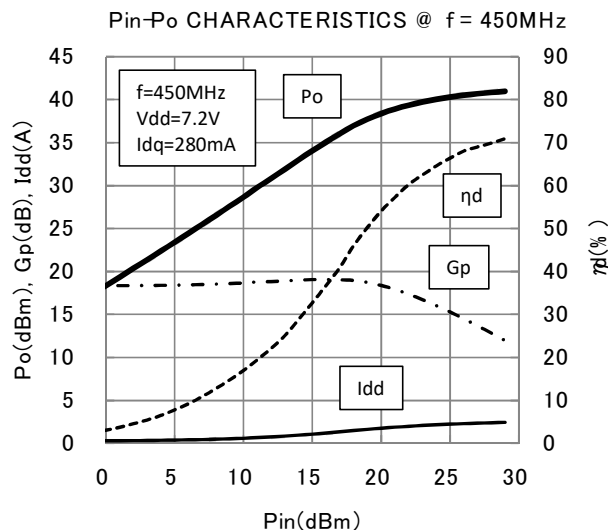


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RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

TYPICAL CHARACTERISTICS (f=450-530MHz)

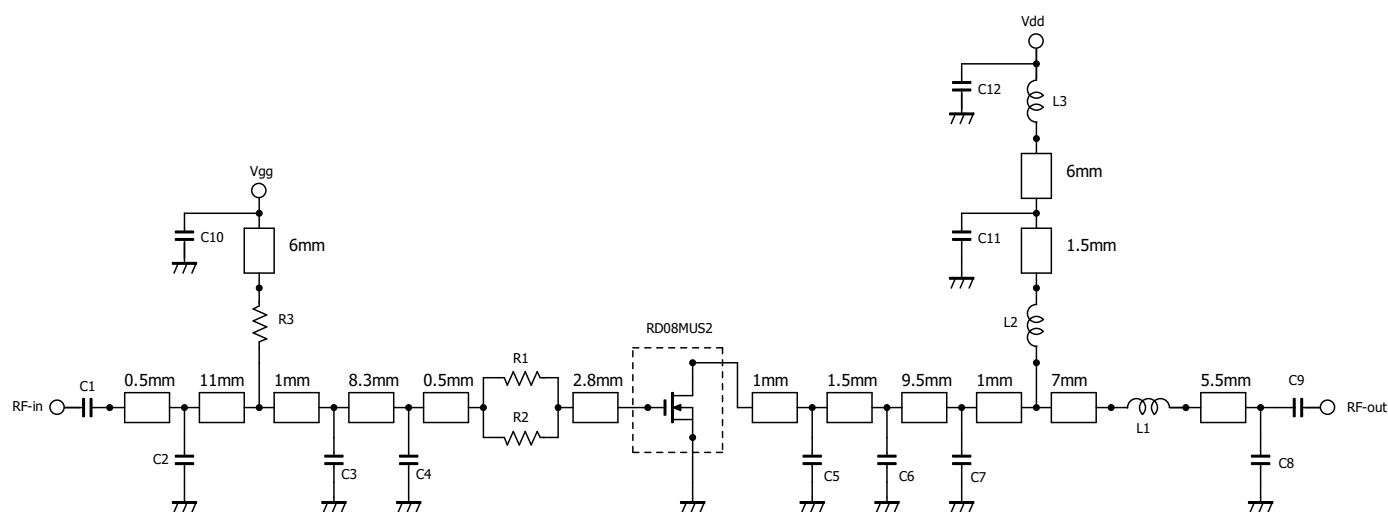
(These are only typical curves and devices are not necessarily guaranteed at these curves.)



RD08MUS2

RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

EQUIVALENT CIRCUITRY for UHF Circuit for f=450-530MHz



<Note>

Board materials : Grass-Epoxy substrate (Er=4.8, t=0.8mm)

Microstrip Line Width = 1.3 mm/ 50 ohm

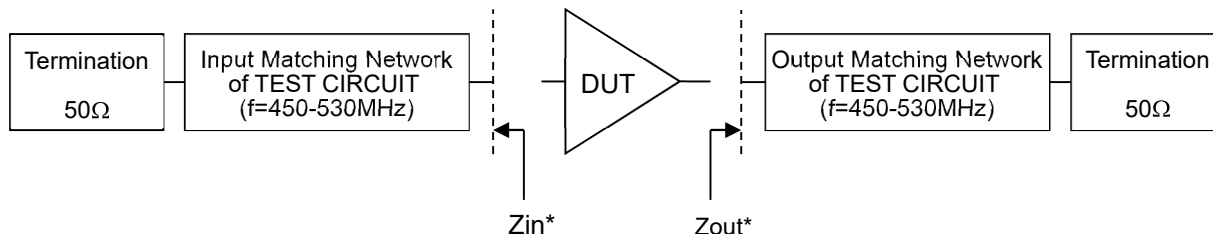
Part	Description	Part number	Manufacturer
C1, 9	100pF	GRM2162C1H101JA01	MURATA MANUFACTURING CO.
C2, 3	5pF	GRM21A5C2D5R0JW01	MURATA MANUFACTURING CO.
C4	39pF	GRM21A5C2D390JW01	MURATA MANUFACTURING CO.
C5, 6	47pF	GQM2192C1H470JB01	MURATA MANUFACTURING CO.
C7, 11	10pF	GRM21A5C2D100JW01	MURATA MANUFACTURING CO.
C8	9pF	GRM21A5C2D9R0JW01	MURATA MANUFACTURING CO.
C10, 12	1000pF	GRM2162C1H102JA01	MURATA MANUFACTURING CO.
C13	22 μ F	UVZ1H220MDD	NICHICON CORPORATION
L1, 2	1.1nH Copper bridge	—	—
L3	25nH Enameled wire 5Turns, Diameter:0.40mm, ϕ 2.46mm (the out side diameter)	4005A	Yoneda Processing Place Co.,Ltd.
R1, 2	1 Ω	RPC05	TAIYOSHA ELECTRIC CO.
R3	2.2 k Ω	RPC05	TAIYOSHA ELECTRIC CO.

RD08MUS2

RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

input / Output Impedance VS. Frequency Characteristics for f=450-530MHz

Method of Measurement

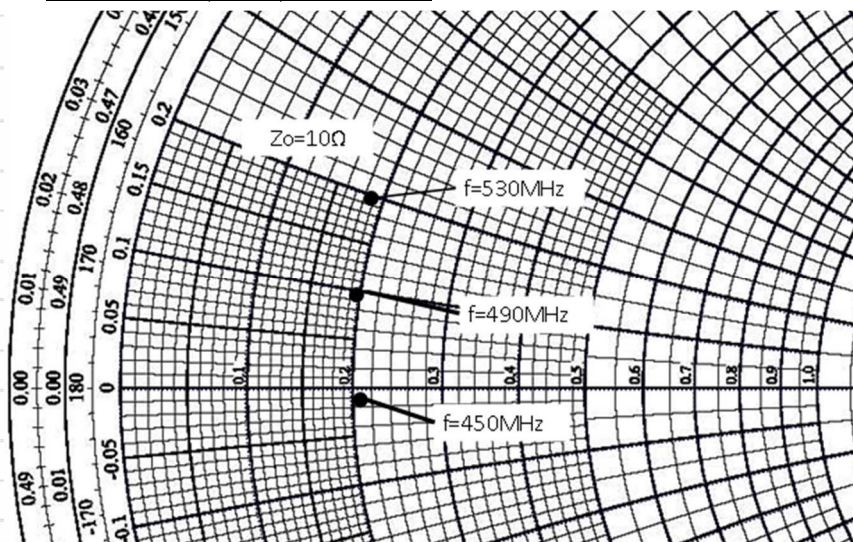


Z_{in}^* : Input Matching Network impedance measured from DUT

Z_{out}^* : Output Matching Network impedance measured from DUT

Z_0 : Characteristic impedance

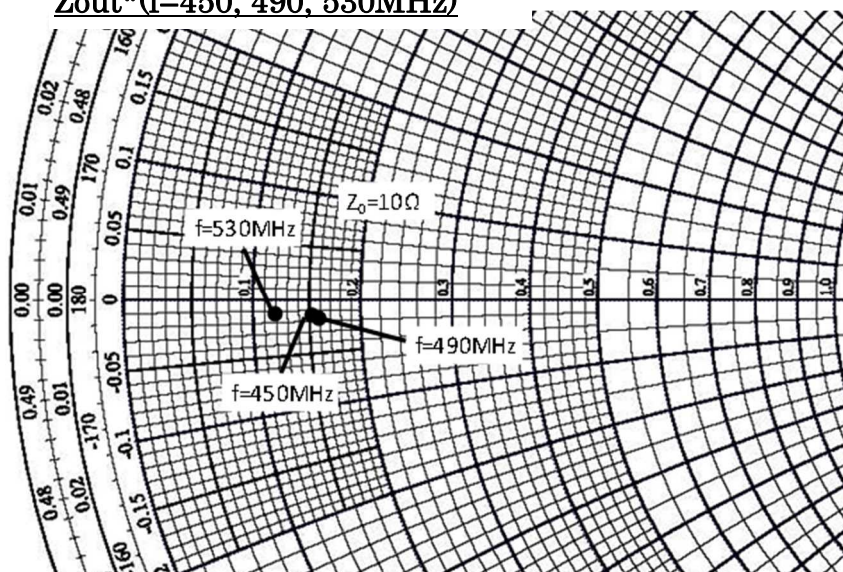
$Z_{in}^*(f=450, 490, 530\text{MHz})$



f (MHz)	Z_{in}^* (Ω)
450	2.07 - j 0.11
490	1.98 + j 0.98
530	1.86 + j 1.98

Z_{in}^* : Complex conjugate of input impedance

$Z_{out}^*(f=450, 490, 530\text{MHz})$



f (MHz)	Z_{out}^* (Ω)
450	1.53 - j 0.12
490	1.61 - j 0.16
530	1.21 - j 0.12

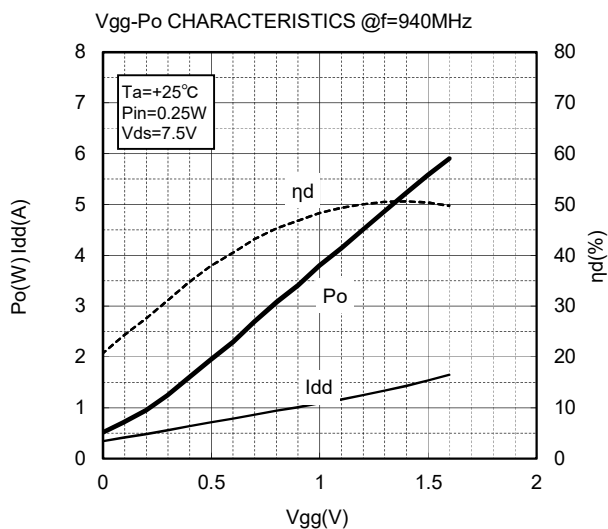
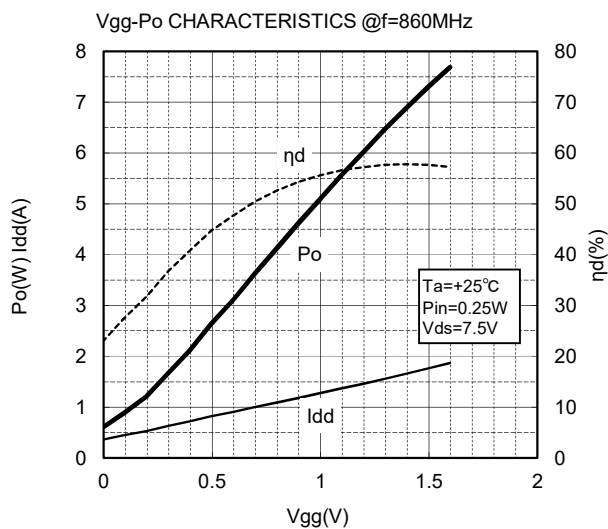
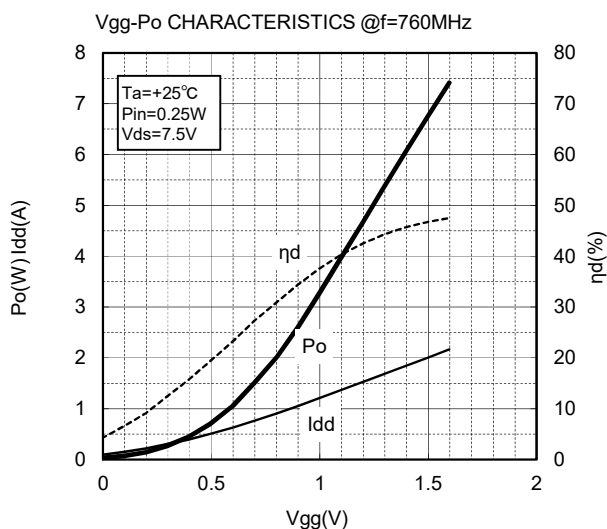
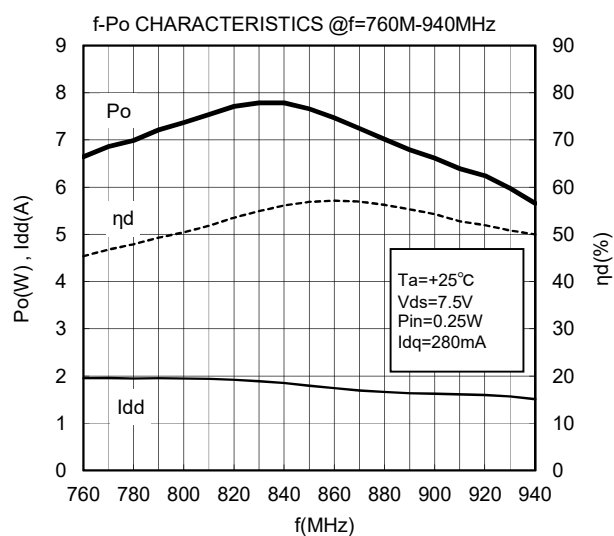
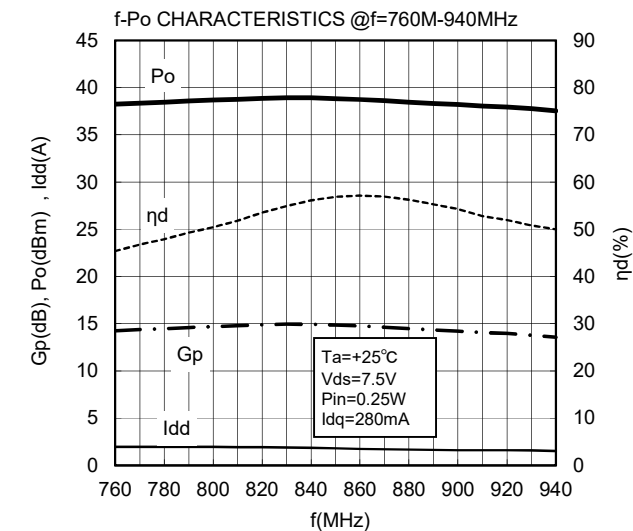
Z_{out}^* : Complex conjugate of output impedance

RD08MUS2

RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

TYPICAL CHARACTERISTICS ($f=760\text{-}940\text{MHz}$, $T_a=+25^\circ\text{C}$)

(These are only typical curves and devices are not necessarily guaranteed at these curves.)

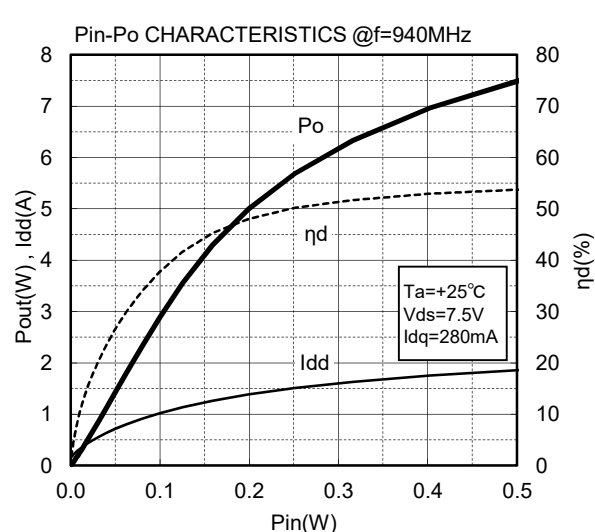
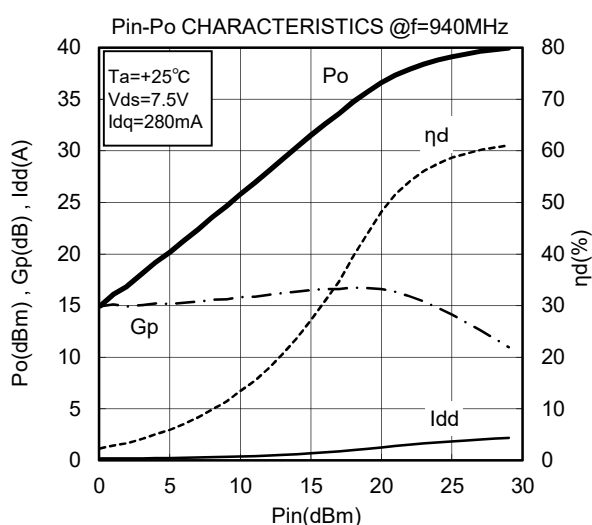
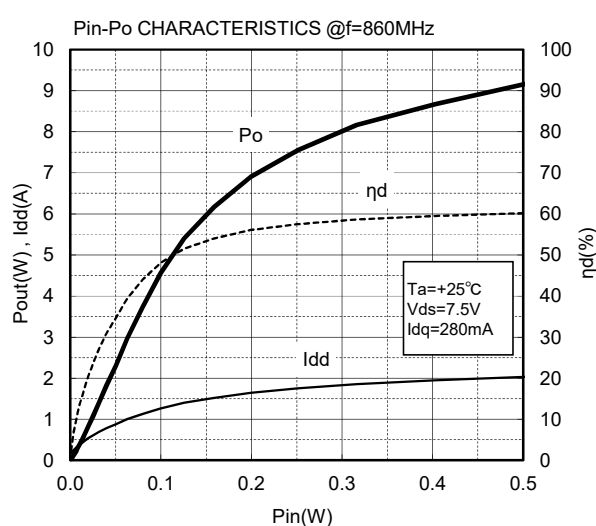
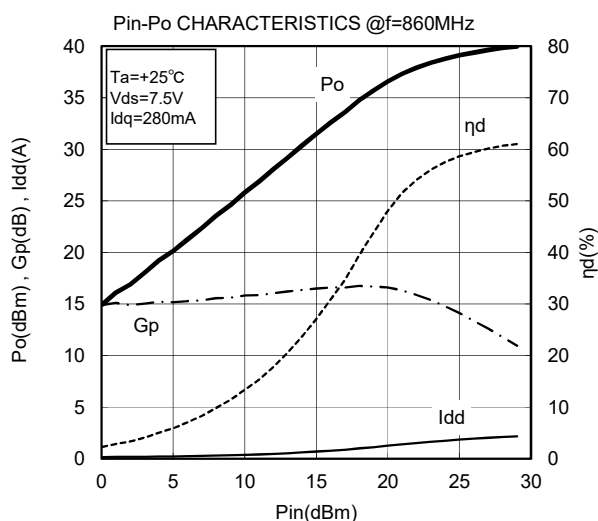
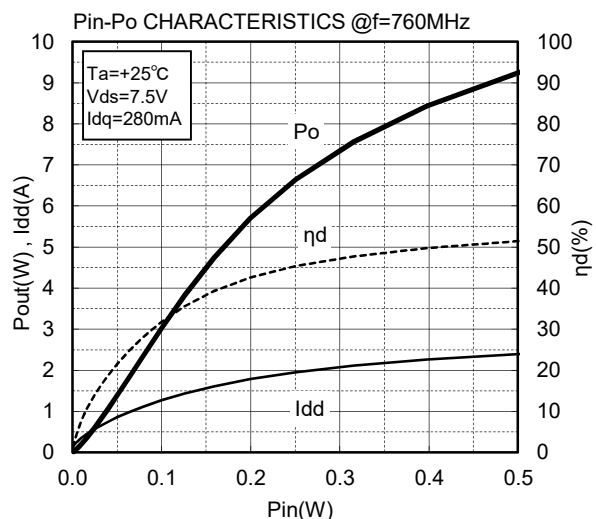
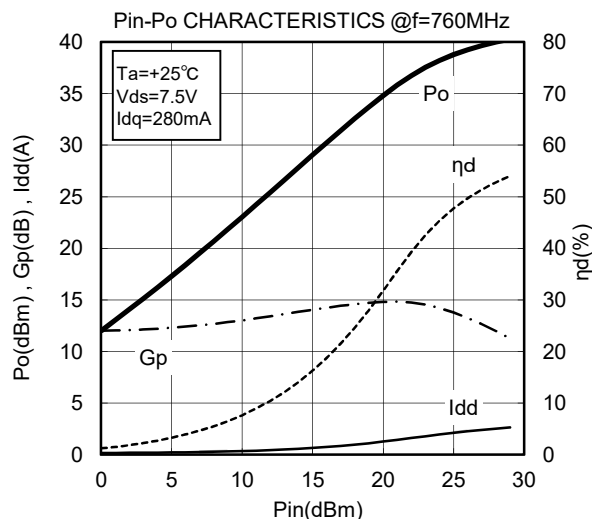


RD08MUS2

RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

TYPICAL CHARACTERISTICS (f=760-940MHz)

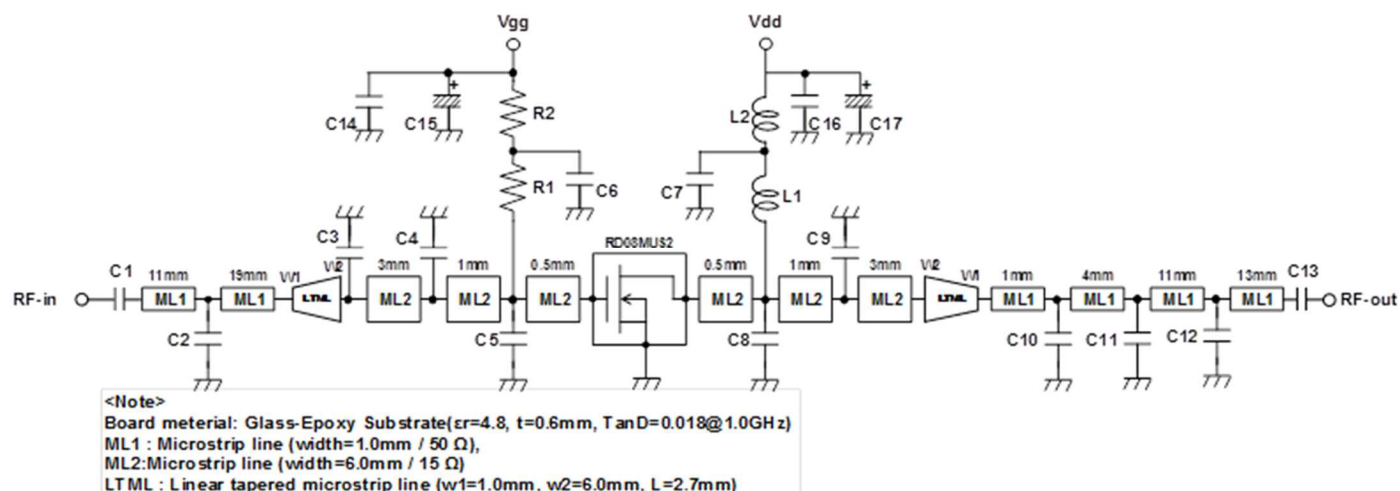
(These are only typical curves and devices are not necessarily guaranteed at these curves.)



RD08MUS2

RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

EQUIVALENT CIRCUITRY for UHF Circuit for f=760-940MHz



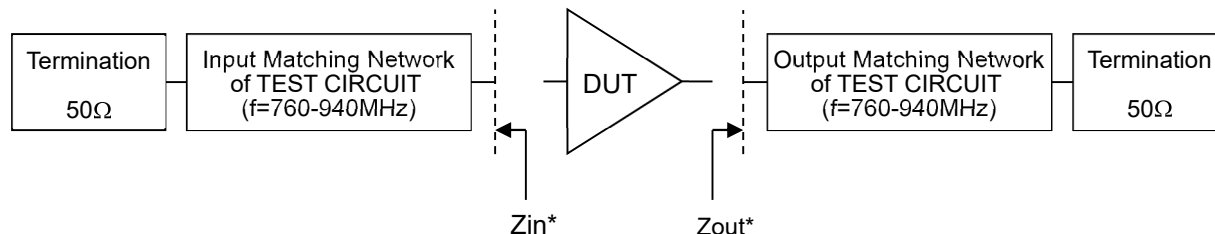
Part	Description	Part number	Manufacturer
C1, C6, C7, C13	100 pF	GQM2195C2E101JB12	MURATA MANUFACTURING CO.
C2	5.1 pF	GQM2195C2E5R1CB12	MURATA MANUFACTURING CO.
C3	8.2 pF	GQM2195C2E8R2CB12	MURATA MANUFACTURING CO.
C4, C5, C8, C9	15 pF	GQM2195C2E150JB12	MURATA MANUFACTURING CO.
C10	6.8 pF	GQM2195C2E6R8CB12	MURATA MANUFACTURING CO.
C11	2 pF	GQM2195C2E2R0CB12	MURATA MANUFACTURING CO.
C12	3.3 pF	GQM2195C2E3R3CB12	MURATA MANUFACTURING CO.
C14, C16	0.022 μF	GRM21B2C1H223JA01	MURATA MANUFACTURING CO.
C15, C17	22 μF	UVZ1H220MDD	NICHICON CORPORATION
L1	14nH Enameled wire 3Turns, Diameter:0.4mm, $\phi 2.46\text{mm}$ (the out side diameter)	4003A	Yoneda Processing Place Co.,Ltd.
L2	25nH Enameled wire 5Turns, Diameter:0.4mm, $\phi 2.46\text{mm}$ (the out side diameter)	4005A	Yoneda Processing Place Co.,Ltd.
R1	100 Ω	RPC05 101-J	TAYOSHAELECTRIC CO.
R2	4.7 k Ω	RPC05 472-J	TAYOSHAELECTRIC CO.

RD08MUS2

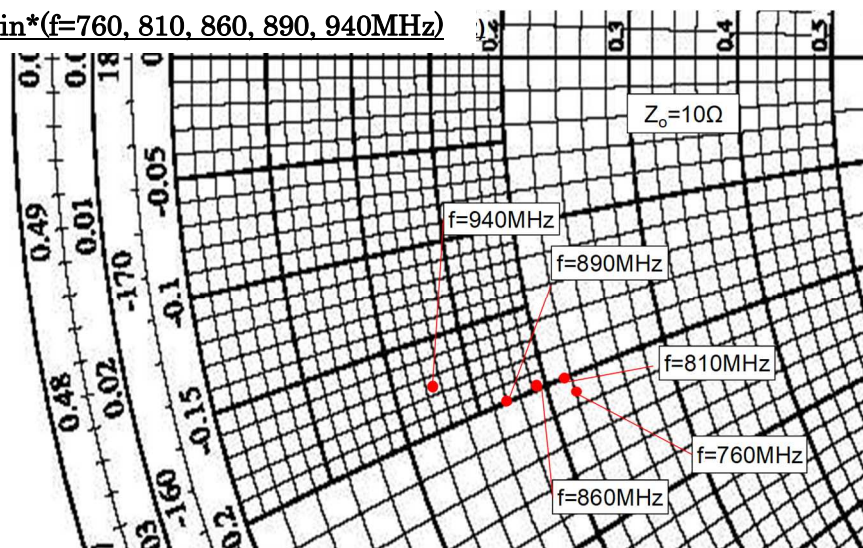
RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

Input / Output Impedance VS. Frequency Characteristics for f=760-940MHz

Method of Measurement

 Z_{in}^* : Input Matching Network impedance measured from DUT Z_{out}^* : Output Matching Network impedance measured from DUT Z_0 : Characteristic impedance

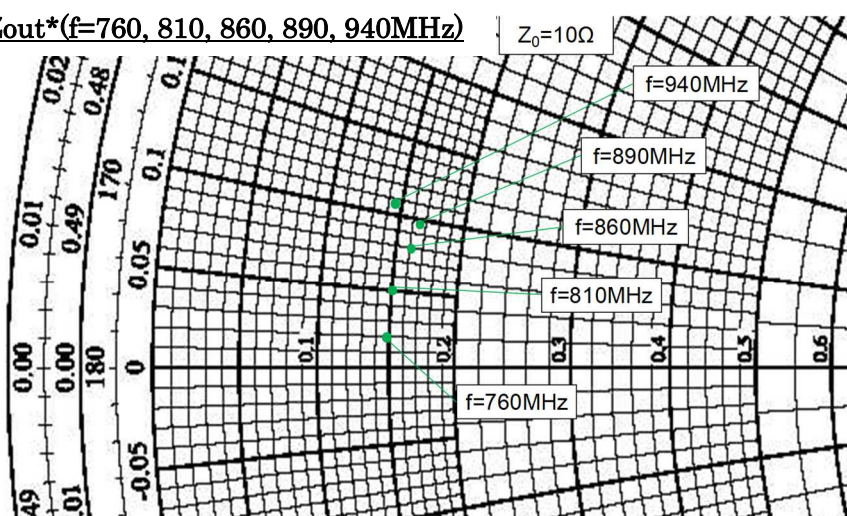
$Z_{in}^*(f=760, 810, 860, 890, 940\text{MHz})$



f (MHz)	Z_{in}^* (Ω)
760	2.17 - j 2.07
810	2.16 - j 2.00
860	1.97 - j 2.02
890	1.72 - j 2.01
940	1.24 - j 1.77

 Z_{in}^* : Complex conjugate of input impedance

$Z_{out}^*(f=760, 810, 860, 890, 940\text{MHz})$



f (MHz)	Z_{out}^* (Ω)
760	1.49 + j 0.12
810	1.48 + j 0.52
860	1.60 + j 0.79
890	1.64 + j 0.95
940	1.42 + j 1.07

 Z_{out}^* : Complex conjugate of output impedance

RD08MUS2

RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

RD08MUS2 S-Parameter data (Vdd=7.2V, Id=280mA)

Freq. (MHz)	S11		S21		S12		S22	
	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)
100	0.84	-171	9.78	78	0.02	-10	0.77	-170
135	0.85	-172	7.09	72	0.01	-15	0.78	-171
155	0.86	-173	6.07	69	0.01	-18	0.79	-171
175	0.86	-173	5.29	66	0.01	-21	0.80	-171
200	0.87	-174	4.52	62	0.01	-24	0.81	-171
250	0.88	-175	3.42	56	0.01	-29	0.83	-172
300	0.89	-175	2.69	50	0.01	-34	0.85	-172
350	0.91	-176	2.16	45	0.01	-38	0.87	-173
380	0.91	-177	1.92	42	0.01	-40	0.88	-174
400	0.92	-177	1.78	40	0.01	-41	0.88	-174
435	0.92	-177	1.56	37	0.01	-43	0.89	-174
450	0.92	-178	1.48	36	0.01	-43	0.90	-174
470	0.93	-178	1.38	34	0.01	-44	0.90	-175
500	0.93	-178	1.25	32	0.01	-45	0.91	-175
527	0.94	-179	1.15	31	0.01	-46	0.91	-175
550	0.94	-179	1.07	29	0.01	-47	0.91	-176
600	0.94	-180	0.93	26	0.01	-48	0.92	-176
650	0.95	179	0.81	24	0.01	-48	0.93	-177
700	0.95	179	0.71	21	0.00	-47	0.94	-178
750	0.95	178	0.64	19	0.00	-45	0.94	-178
800	0.96	177	0.57	17	0.00	-41	0.95	-179
850	0.96	177	0.51	15	0.00	-38	0.95	-180
900	0.96	176	0.46	14	0.00	-31	0.95	180
950	0.96	175	0.42	12	0.00	-22	0.95	179
1000	0.96	175	0.38	10	0.00	-7	0.96	179

RD08MUS2

RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

ATTENTION:

- 1.High Temperature ; This product might have a heat generation while operation,Please take notice that have a possibility to receive a burn to touch the operating product directly or touch the product until cold after switch off. At the near the product,do not place the combustible material that have possibilities to arise the fire.
- 2.Generation of High Frequency Power ; This product generate a high frequency power. Please take notice that do not leakage the unnecessary electric wave and use this products without cause damage for human and property per normal operation.
- 3.Before use; Before use the product,Please design the equipment in consideration of the risk for human and electric wave obstacle for equipment.

PRECAUTIONS FOR THE USE OF MITSUBISHI SILICON RF POWER DEVICES:

1. The specifications of mention are not guarantee values in this data sheet. Please confirm additional details regarding operation of these products from the formal specification sheet. For copies of the formal specification sheets, please contact one of our sales offices.
- 2.RA series products (RF power amplifier modules) and RD series products (RF power transistors) are designed for consumer mobile communication terminals and were not specifically designed for use in other applications.
In particular, while these products are highly reliable for their designed purpose, they are not manufactured under a quality assurance testing protocol that is sufficient to guarantee the level of reliability typically deemed necessary for critical communications elements and In the application, which is base station applications and fixed station applications that operate with long term continuous transmission and a higher on-off frequency during transmitting, please consider the derating, the redundancy system, appropriate setting of the maintain period and others as needed. For the reliability report which is described about predicted operating life time of Mitsubishi Silicon RF Products , please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor.
3. RD series products use MOSFET semiconductor technology. They are sensitive to ESD voltage therefore appropriate ESD precautions are required.
4. In the case of use in below than recommended frequency, there is possibility to occur that the device is deteriorated or destroyed due to the RF-swing exceed the breakdown voltage.
5. In order to maximize reliability of the equipment, it is better to keep the devices temperature low. It is recommended to utilize a sufficient sized heat-sink in conjunction with other cooling methods as needed (fan, etc.) to keep the channel temperature for RD series products lower than 120deg/C(in case of Tchmax=150deg/C) ,140deg/C(in case of Tchmax=175deg/C) under standard conditions.
6. Do not use the device at the exceeded the maximum rating condition. In case of plastic molded devices, the exceeded maximum rating condition may cause blowout, smoldering or catch fire of the molding resin due to extreme short current flow between the drain and the source of the device. These results causes in fire or injury.
7. For specific precautions regarding assembly of these products into the equipment, please refer to the supplementary items in the specification sheet.
8. Warranty for the product is void if the products protective cap (lid) is removed or if the product is modified in any way from it's original form.
9. For additional "Safety first" in your circuit design and notes regarding the materials, please refer the last page of this data sheet.

RD08MUS2

RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

10. Please avoid use in the place where water or organic solvents can adhere directly to the product and the environments with the possibility of caustic gas, dust, salinity, etc.

Reliability could be markedly decreased and also there is a possibility failures could result causing a serious accident. Likewise, there is a possibility of causing a serious accident if used in an explosive gas environment. Please allow for adequate safety margin in your designs.

11. Please refer to the additional precautions in the formal specification sheet.

Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

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RD08MUS2

RoHS Compliance, Silicon MOSFET Power Transistor, 527MHz, 7.5W, 7.2V

Main Revision for this Edition

No	Date	Revision	
		Pages	Points
注意	-	-	・pdf 化するときに本ページ(改訂履歴部分)は削除すること。 ・最後のページのコピータイトの年数は初版発行時の年数にすること。
0	2016.12.26	1-11	New
1	2017.3.1	8	回路インピーダンスリストの誤記を修正
2	2017.7.5	5-8,12-20	VHF, UHF-2, 7/8/900MHz 帯の EVB データを追加
3	2019.6.19	1	Deleted "RoHS compliance is indicating by the letter "G" after the Lot Marking"
4	2022.9.14	16	Impedance chart added.
5	2024.2.9	1	ORDERING INFORMATION を追加 RoHS COMPLIANT の文章から形名を削除 (元: RD08MUS2-501, T512, T514 is EU RoHS compliant.)
		7,11, 15,19	部品表から部品の型名とメーカーの情報を削除
6	2024.4.4	1	ORDERING INFORMATION を Cu ワイヤ品に変更(500 番台を 600 番台へ変更) RD08MUS2-501 → RD08MUS2-601 RD08MUS2-T512 → RD08MUS2-T612 RD08MUS2-T514 → RD08MUS2-T614